



PJQ2463A

60V P-Channel Enhancement Mode MOSFET

| | | | |
|----------------|--------------|----------------|---------------|
| Voltage | -60 V | Current | -3.2 A |
|----------------|--------------|----------------|---------------|

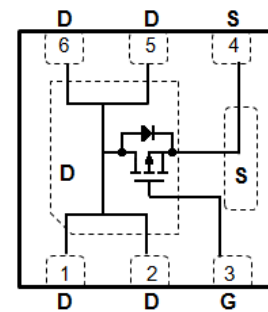
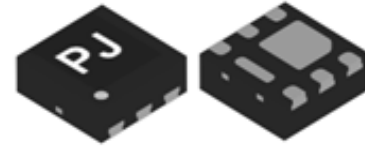
Features

- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-3A < 105m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-2A < 145m\Omega$
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN2020B-6L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0003 ounces, 0.0086 grams

DFN2020B-6L



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

| PARAMETER | | SYMBOL | LIMIT | UNITS |
|--|---------------------------------|-----------------|---------|---------------------------|
| Drain-Source Voltage | | V_{DS} | -60 | V |
| Gate-Source Voltage | | V_{GS} | +20 | |
| Continuous Drain Current (Note 4) | | I_D | -3.2 | A |
| Pulsed Drain Current (Note 1) | | I_{DM} | -12.8 | |
| Power Dissipation | $T_a=25^\circ\text{C}$ | P_D | 2 | W |
| | Derate above 25°C | | 16 | mW/ $^\circ\text{C}$ |
| Operating Junction and Storage Temperature Range | | T_J, T_{STG} | -55~150 | $^\circ\text{C}$ |
| Typical Thermal Resistance | | $R_{\theta JA}$ | 62.5 | $^\circ\text{C}/\text{W}$ |
| - Junction to Ambient (Note 4,5) | | | | |



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Electrical Characteristics (T_A=25°C unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNITS |
|---|---------------------|---|------|-------|------|-------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =-250uA | -60 | - | - | V |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =-250uA | -1 | -1.7 | -2.5 | |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} =-10V, I _D =-3A | - | 87 | 105 | mΩ |
| | | V _{GS} =-4.5V, I _D =-2A | - | 120 | 145 | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =-60V, V _{GS} =0V | - | - | -1 | uA |
| Gate-Source Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0V | - | - | ±100 | nA |
| Dynamic (Note 6) | | | | | | |
| Total Gate Charge | Q _g | V _{DS} =-30V, I _D =-3A, V _{GS} =-10V (Note 1,2) | - | 10 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 1.6 | - | |
| Gate-Drain Charge | Q _{gd} | | - | 3 | - | |
| Input Capacitance | C _{iss} | V _{DS} =-30V, V _{GS} =0V, f=1MHZ | - | 785 | - | pF |
| Output Capacitance | C _{oss} | | - | 175 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 112 | - | |
| Turn-On Delay Time | t _{d(on)} | V _{DS} =-30V, R _L =30Ω V _{GS} =-10V, R _G =6.2Ω (Note 1,2) | - | 8 | - | ns |
| Turn-On Rise Time | t _r | | - | 15 | - | |
| Turn-Off Delay Time | t _{d(off)} | | - | 43 | - | |
| Turn-Off Fall Time | t _f | | - | 8.4 | - | |
| Drain-Source Diode | | | | | | |
| Maximum Continuous Drain-Source Diode Forward Current | I _S | --- | - | - | -1.5 | A |
| Diode Forward Voltage | V _{SD} | I _S =-1A, V _{GS} =0V | - | -0.75 | -1 | V |

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J = 25°C.
4. The maximum current rating is package limited.
5. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

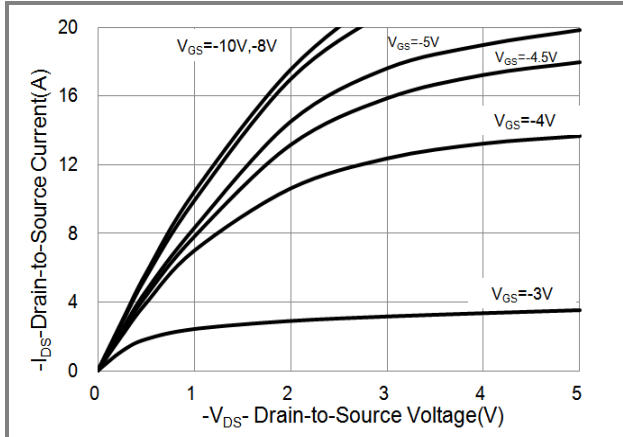


Fig.1 On-Region Characteristics

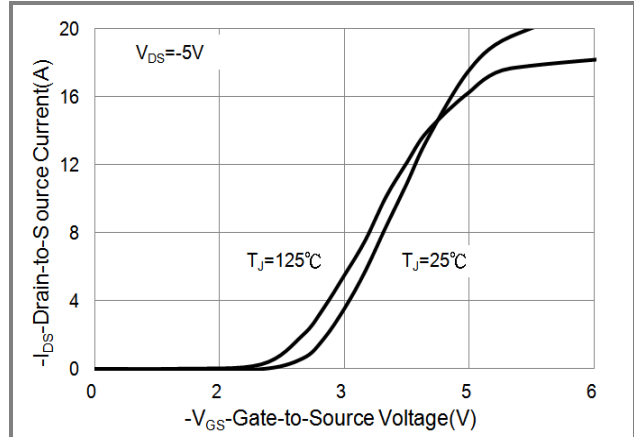


Fig.2 Transfer Characteristics

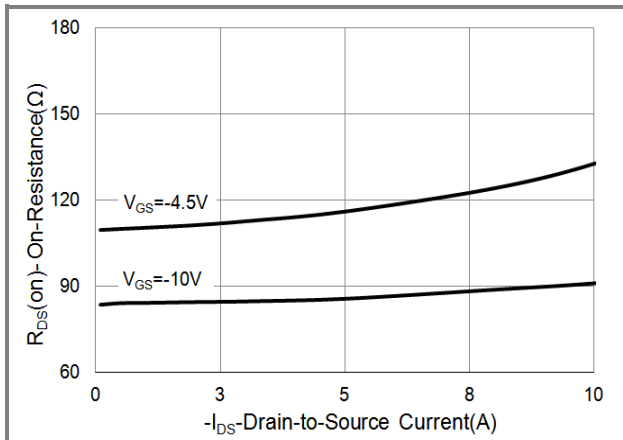


Fig.3 On-Resistance vs. Drain Current

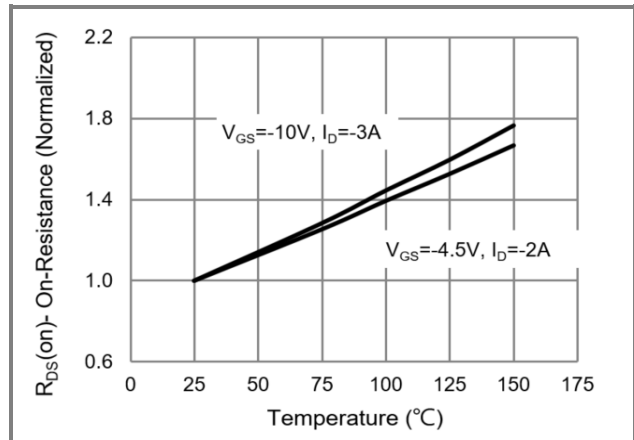


Fig.4 On-Resistance vs. Junction temperature

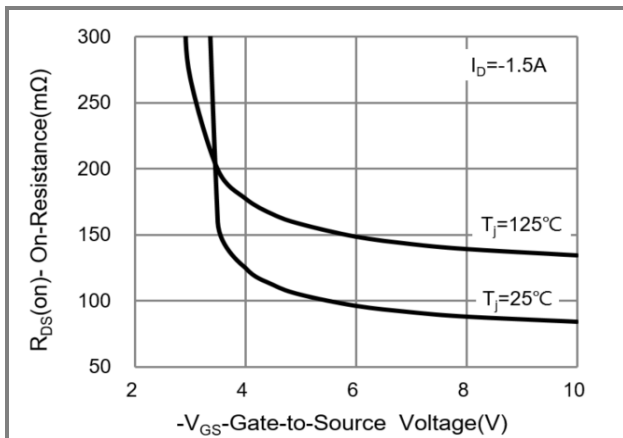


Fig.5 On-Resistance Variation with V_{GS}

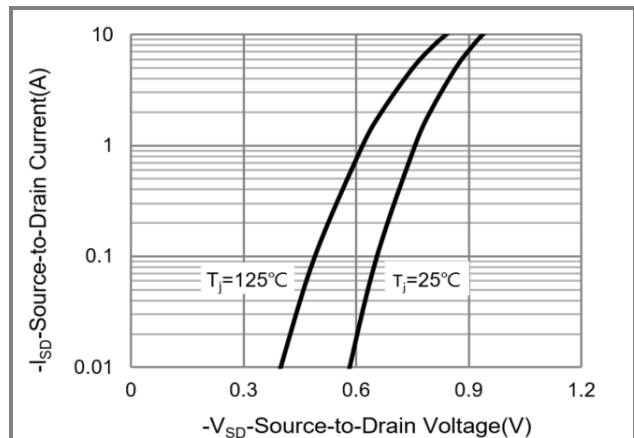


Fig.6 Body Diode Characteristics



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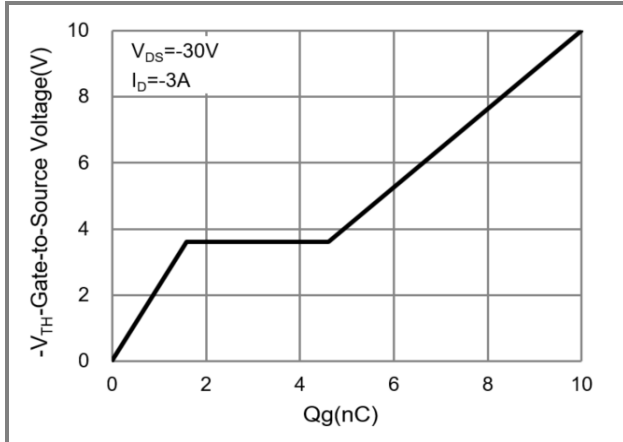


Fig.7 Gate-Charge Characteristics

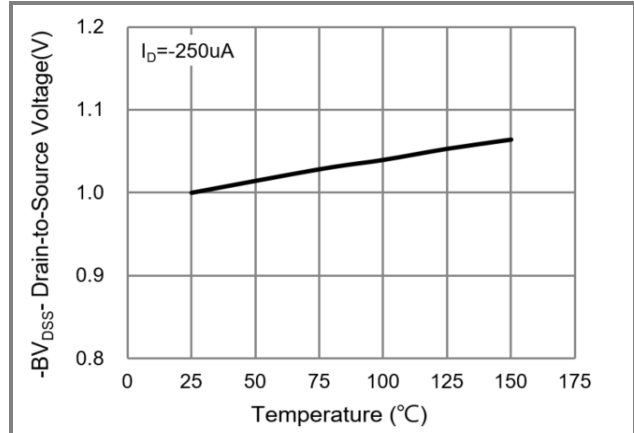


Fig.8 Breakdown Voltage Variation vs. Temperature

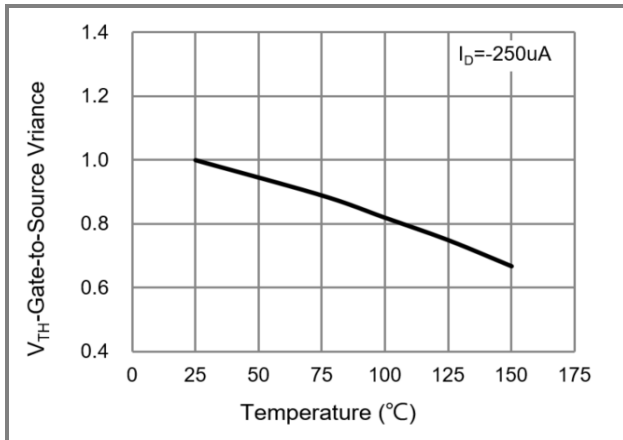


Fig.9 Threshold Voltage Variation with Temperature

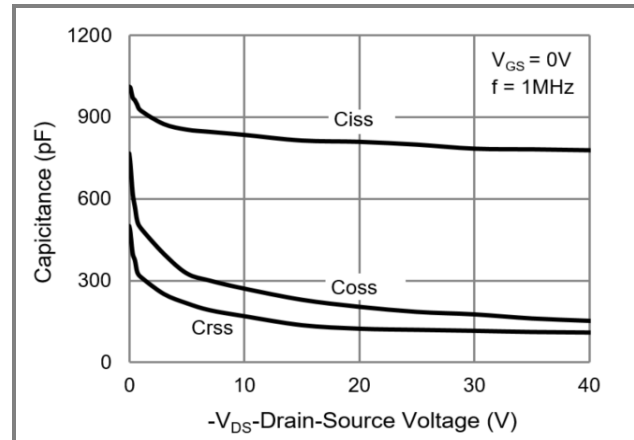


Fig.10 Capacitance vs. Drain-Source Voltage



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Part No. Packing Code Version

| Part No. Packing Code | Package Type | Packing Type | Marking | Version |
|-----------------------|--------------|------------------|---------|--------------------------------|
| PJQ2463A_R1_00001 | DFN2020B-6L | 3K pcs / 7" reel | 463 | Halogen free RoHS compliant |

Packaging Information & Mounting Pad Layout

